# Abstracts

## A 0.1 µm GaAs MESFET Technology for Ultra-High-Speed Digital and Analog ICs

*M. Tokumitsu, M. Hirano, K. Murata, Y. Imai and K. Yamasaki. "A 0.1 µm GaAs MESFET Technology for Ultra-High-Speed Digital and Analog ICs." 1994 MTT-S International Microwave Symposium Digest 94.3 (1994 Vol. III [MWSYM]): 1629-1632.*

A 0.1 µm gate-length GaAs IC technology is reported. A 48.3 GHz dynamic-frequency divider, and an amplifier with 20 dB gain and 17.5 GHz bandwidth are successfully fabricated by integrating over 100 GHz cut-off frequency MESFETs by using a new BP-LDD device structure.

❑ Return to main document.